

## Observation of Universal Thermopower Fluctuations

B. L. Gallagher, T. Galloway, P. Beton, and J. P. Oxley

*Physics Department, University of Nottingham, Nottingham NG7 2RD, United Kingdom*

S. P. Beaumont, S. Thoms, and C. D. W. Wilkinson

*Department of Electronic and Electrical Engineering, University of Glasgow,  
Glasgow GL2 8QQ, United Kingdom*

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We have measured the thermopower of small  $n^+$ -type GaAs wires using a novel electron heating technique. The results show very large fluctuations which are in good agreement with existing theories. We believe this to be the first observation of universal thermopower fluctuations.

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In the usual semiclassical theory of electron conduction the interference between scattered waves is neglected since it is assumed that such effects will be averaged away. For conductors of size comparable with the electron phase-coherence length such averaging breaks down and these interference effects become intrinsically non-self-averaging, giving rise to universal conductance fluctuations as a function of magnetic field<sup>1,2</sup> or Fermi energy.<sup>3</sup> Other transport coefficients are also expected to show aperiodic fluctuations of which the thermopower is predicted to show the most dramatic behavior.<sup>4</sup>

A simple estimate of the diffusion thermopower fluctuations for a degenerate conductor can be obtained from the Mott formula:

$$S = - \frac{\pi^2}{3} \frac{k}{|e|} \frac{kT}{G} \left. \frac{dG}{dE} \right|_{E_F}, \quad (1)$$

where  $G$  is the electrical conductance,  $E_F$  is the Fermi energy, and  $k$  is Boltzmann's constant. Since quantum interference effects lead to a conductance which is a rapidly fluctuating function of  $E_F$ , (1) immediately implies that the associated thermopower will fluctuate about zero with a large amplitude. We now replace the derivative by  $\delta G/\Delta E$ , where  $\delta G$  is the rms amplitude of the conductance fluctuations.  $\Delta E$ , their average energy scale, will be the larger of  $kT$ ,  $\hbar D/L_i^2$ , or  $\hbar D/L^2$ , where  $L$  is the specimen length in the direction of the temperature gradient,  $L_i$  is the inelastic-scattering length, and  $D$  is the diffusion coefficient. In our specimens in the temperature range studied,  $kT$  is the largest of these so the rms amplitude of the thermopower fluctuations will be

$$\delta S \approx \beta - \frac{\pi^2}{3} \frac{k}{|e|} \frac{\delta G}{G}, \quad \beta \approx 1. \quad (2)$$

This is only a crude estimate since the Mott formula assumes that  $G$  is slowly varying on energy scales  $kT$  which is untrue in this case. However, detailed theoretical calculations<sup>4,5</sup> show that (2) will still be correct provided that for a phase-coherent subunit  $\delta G/G$  is small, as it is in our specimens. Furthermore, for the case when

$\Delta E = kT$  the prefactor  $\beta$  can be easily calculated. In the Appendix we show that  $\beta = 0.17 \pm 0.01$ . The ratio of  $\delta S$  to  $\delta G/G$  for  $\Delta E = kT$  is thus a simple universal value, independent of temperature, size of specimen, or the degree of disorder. This remarkable result is implicit in Refs. 4 and 5 but is not given the emphasis it deserves. The key result is that the temperature and size dependences of  $\delta S$ , which can be complicated, arise solely from those of  $\delta G/G$ .

The specimens we have studied are  $n^+$ -type GaAs wires fabricated by electron-beam lithography and dry etching from molecular-beam-epitaxy grown layers. They are of physical width  $500 \mu\text{m}$ , thickness  $50 \text{ nm}$ , and length  $190 \mu\text{m}$  with many side arms. The electron concentration derived from Hall and Shubnikov-de Haas measurements is  $1.09 \times 10^{24} \text{ m}^{-3}$ . The electron-transport mean free path (MFP) is about  $50 \text{ nm}$  and the scattering MFP will be smaller than this so a diffusive-transport model should still be valid.

The two-terminal magnetoresistance of a  $9\text{-}\mu\text{m}$  section of wire (Fig. 1) shows that the relatively large conductance fluctuations persist to the highest fields and coexist

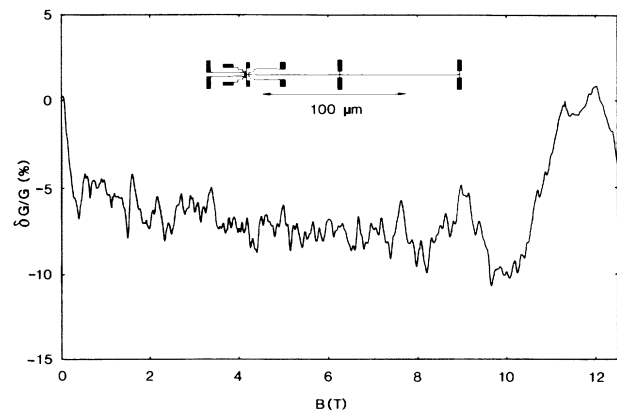


FIG. 1. Two-terminal resistance fluctuations in a  $9\text{-}\mu\text{m}$  section of the wire. The wire resistance at zero field is  $22 \text{ k}\Omega$ . Inset: Wire geometry.

with the high-field Shubnikov-de Haas oscillations. The underlying negative magnetoresistance is due to weak localization and electron-electron interaction effects.

The fundamental problem in measuring thermopower is how to establish a significant temperature difference along such micron-scale devices. In practice, we find that the largest gradients in the lattice temperature which we can establish will only give thermoelectric voltages of a few nanovolts. This is of the same order as the Johnson noise. This has led us to use gradients in the electron temperature produced by electron heating. Such gradients, which are easily established, will give the same result for the diffusion thermopower as the conventional approach, since electron-phonon scattering is unimportant, and will also eliminate the phonon-drag contribution.

In our experiment an electric field is applied along the wire and the thermoelectric voltage,  $V_{AB}$ , is measured between the ends of the side arms (see Fig. 2). The electrons at  $C$  will be at a temperature  $T_{E\max}$  and those at  $A$  and  $B$  close to the lattice temperature  $T_L$  since the energy relaxation length is  $\sim 2 \mu\text{m}$  and the distance  $AC=CB=4.5 \mu\text{m}$ . The local electron temperature will be well defined since the electron-electron scattering time ( $\tau_e \sim 6 \times 10^{-12} \text{ s}$ ) is far shorter than the electron-phonon scattering time ( $\tau_{ep} \sim 6 \times 10^{-10} \text{ s}$ ) in these specimens.<sup>2</sup> In fact,  $T_{E\max}$  will itself show fluctuations, but this is not important as they will only be  $\sim 1\%$ . For a homogeneous conductor the voltages  $V_{AC}$  and  $V_{CB}$  would cancel, but the thermopower fluctuations in each arm are uncorrelated and so simply add in an rms fashion. Another unique consequence of this technique is that the symmetry of the temperature distributions allows an absolute rather than a relative thermopower to be determined. This can be seen from Fig. 2. Points  $A$  and  $B$  are the junctions between the sample and the external circuitry and these will be the same temperature. Point  $C$  is at a higher temperature but is internal to the sample; the nor-

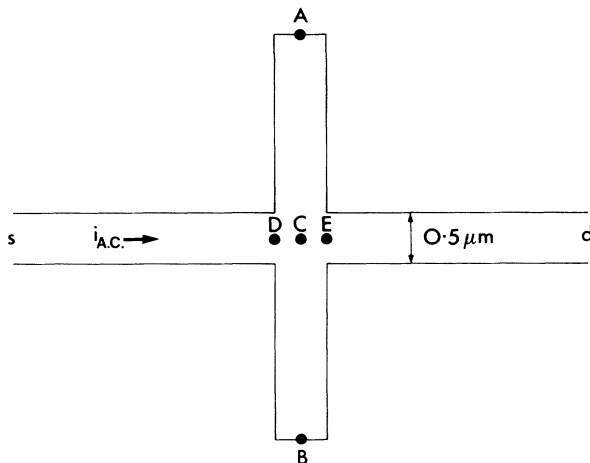


FIG. 2. Detail of the wire geometry. Length  $AB$  is  $9 \mu\text{m}$ .

mal circuit of a hot junction and a cold junction between differing materials does not exist. In practice, the field along the wire is alternating at low frequency so any contribution to  $V_{AB}$  from the Hall effect is eliminated. The calibration of  $T_E(V_{ac})$  is obtained from  $G(V_{ac})$  and  $G(T_L)$  which are measured to high accuracy with a six-decade inductive ratio bridge. This "hot-electron thermopower" technique is an extension of our previous work on the thermopower of 2D electron systems.<sup>6</sup>

The measurements are made by recording the dc voltage ( $V_{AB}$ ) between points  $A$  and  $B$  as the magnetic field is slowly swept (typically  $0.5 \text{ T/min}$ ). Figure 3 shows a series of measured thermoelectric voltages. One can see that they show the expected large oscillations about zero. At higher fields we find no contribution from the Shubnikov-de Haas oscillation as this will be the same in each arm and thus eliminated. Such traces are totally reproducible over weeks so long as the wire is kept in the dark at helium temperatures. In Fig. 4 the ratio of  $\delta V/(\Delta G/G)$  is plotted against  $T_{E\max} - T_L$ , the value of  $\Delta G/G$  being taken at  $T_{E\max}$  since, as we will show later, the dominant contribution to  $\delta V$  comes from the hotter regions. One sees that the data for different  $T_L$  all fall close to the same line as expected and agree well with that predicted by Eq. (2), except that the results are a factor of about 3 larger than the theory predicts. However, this comparison implicitly assumes that each phase-coherent subunit contributes equally to the fluctuations in conductivity and thermoelectric voltage, i.e., that the temperature gradient is linear, which will not be true.

The full form of  $T_E(x)$  along the wire may be obtained by numerical solution of the diffusion equation provided that the energy relaxation length  $L_E(T_E, T_L)$  is known.<sup>7</sup> This we obtain from our calibration of  $T_E(V_{ac})$

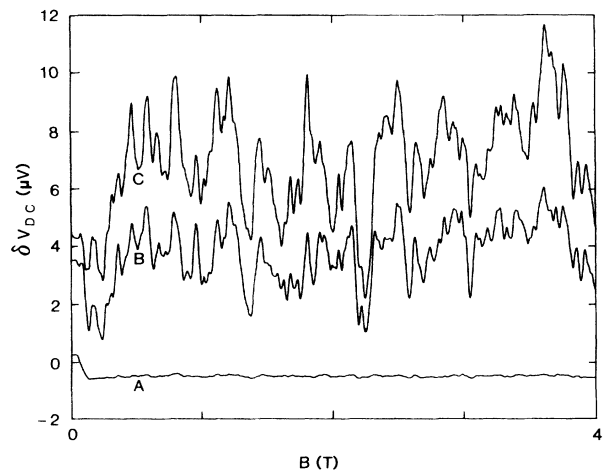


FIG. 3. dc thermoelectric voltage fluctuations due to the electron temperature gradient. Heating voltage ( $ac$ ) across  $DE$  is  $0, 17,$  and  $45 \mu\text{V}$  for traces  $A, B,$  and  $C$ . Trace  $B$  has been offset by  $4 \mu\text{V}$  and  $C$  by  $7 \mu\text{V}$ .

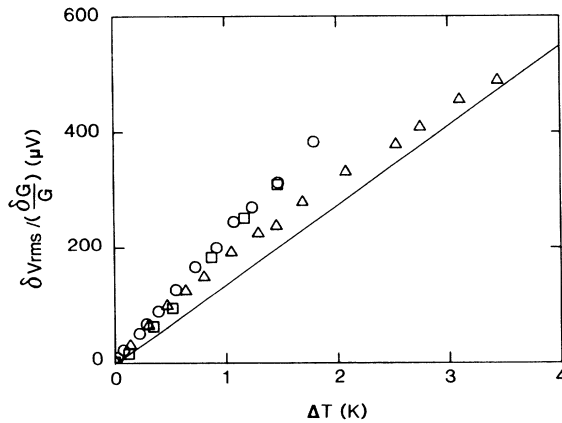


FIG. 4. rms dc thermoelectric voltage fluctuations as a function of  $\Delta T = T_{E\max} - T_L$  compared with the theoretical prediction assuming a linear temperature gradient. The theoretical values have been increased by a factor of 2. Data points:  $T_L = 1.08$  K ( $\Delta$ ),  $2.00$  K ( $\circ$ ), and  $4.00$  K ( $\square$ ).

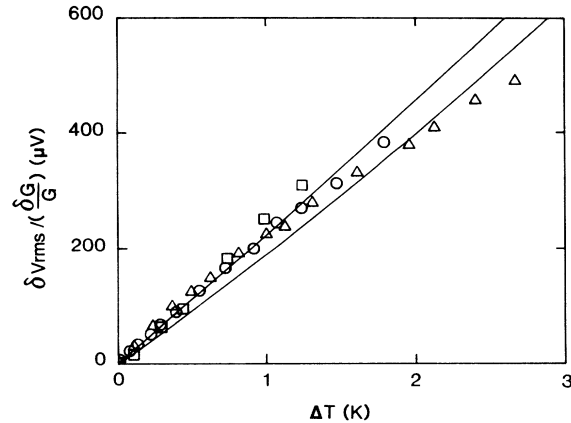


FIG. 5. rms dc thermoelectric voltage fluctuations as a function of  $\Delta T = T_{E\max} - T_{E\min}$  compared with the theoretical predictions for the true temperature gradient. Upper line prediction for  $T_L = 4$  K; lower line for  $T_L = 1$  K. The predicted values have been increased by a factor of 2. Data points:  $T_L = 1.08$  K ( $\Delta$ ),  $2.00$  K ( $\circ$ ), and  $4.00$  K ( $\square$ ).

by use of the energy-balance equation.<sup>7</sup> The phase breaking length,  $L_\phi$ , should be given by  $(\hbar D/kT)^{1/2}$ . To check this  $L_\phi$  is calculated by assuming that for each phase-coherence subunit  $\delta G = e^2/h$  and adding these in an rms fashion. We obtain good agreement in magnitude and temperature with the expected form. This then allows us to calculate the temperature difference across each subunit and to directly calculate the expected thermoelectric voltage for a given  $T_{E\max}$  and  $T_L$ . The predictions of this full theory are compared with the experimental data in Fig. 5. In this case the values of  $\delta G/G$  are taken at the appropriate average temperature. The true temperature difference along the wire is also used since the calculated  $T_{E\min}$  can be slightly larger than  $T_L$ . One sees that the good agreement with the predicted form is retained and that now the results are a factor of 2 greater than the prediction. These calculated thermopowers are close to the prediction of the simple theory. There are two reasons for this. First, we choose the distances  $AC$  and  $CB$  to be approximately  $2L_E$  so that  $T_{E\min}$  is not very much larger than  $T_L$  and the departure from linearity not too dramatic. Second, we find that the ratio  $L_E/L_\phi$  is almost constant over the temperature range studied which leads to the temperature difference across each subunit being a weak function of distance along the wire.

We feel confident that these voltages are indeed thermoelectric. It is difficult to see what other effects could mimic the observed behavior. The EM electronics N1A nanovoltmeter used to measure the dc voltages has an input bias current of typically  $< 5$  pA with an upper bound of 20 pA, and an effective input impedance of 1 G  $\Omega$ . Therefore a fluctuating voltage of larger than 4 nV could not be produced due to the input bias current. Further, such currents would result in traces looking like Fig. 1 including the Shubnikov-de Haas oscillations at

high fields. The structure observed was also totally unaffected by sweep rate or direction so induced voltages are of no importance. A fluctuating Hall-like voltage which *did not* reverse sign with current is perhaps conceivable but this would require  $\sim 10\%$  of the voltage dropped between  $D$  and  $E$  (Fig. 2) to appear perpendicular to the current direction. More importantly, such a contribution would surely be linear in  $V_{ac}$  and this is very far from the case. In fact, we find the linear dependence upon the temperature difference most convincing because this difference is both strongly nonlinear in  $V_{ac}$  and strongly dependent upon  $T_L$ . We have also studied the rectification of alternating-voltage signals due to the non-Ohmic conduction<sup>8</sup> in these systems and can discount this as a possible cause of the voltage we measure.

In conclusion, we have employed a novel hot-electron technique to measure the thermopower of a mesoscopic conductor. The thermoelectric voltages obtained are large compared with those one might expect to arise from any other source. The results agree with theory in form, dependence on temperature, and temperature gradient. The absolute magnitudes differ from the theoretical predictions by a factor of 2. We feel that these results show unequivocally the existence of universal thermopower fluctuations.

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*Note added.*—This technique has recently been employed to successfully measure the thermopower of quantum point contacts.<sup>9</sup>

*Appendix: Calculation of the thermopower fluctuations.*—If we take the case when  $\delta G_{rms} \leq G$ , the gen-

eral expression for the thermopower is

$$\delta S_{\text{rms}} = (G |e| T)^{-1} \left[ \int_0^\infty \int_0^\infty \frac{df}{d\epsilon} \frac{df'}{d\epsilon'} (\epsilon - \mu)(\epsilon' - \mu) F(\epsilon - \epsilon') d\epsilon d\epsilon' \right]^{1/2}, \quad (\text{A1})$$

where  $f$  is the Fermi function,  $\mu$  is the chemical potential, and  $F(x)$  is the conductivity correlation function. In the case  $\mu \gg kT = E_c$  Eq. (2) is obtained and the value of  $\beta$  is found by numerical integration to be insensitive to the form of the correlation function: the values for  $\beta$  being 0.18, 0.17, and 0.16 for  $F(x)$  of Gaussian, semielliptic, and inverted parabolic, respectively. These values are much less than those implied in Ref. 4. For  $\mu \gg kT \ll E_c$ ,  $\beta$  is replaced by  $\gamma kT/E_c$ .  $\gamma$  is now sensitive to the detailed form of  $F(x)$  being  $\sqrt{2}$  for the Gaussian and inverted parabolic forms but only half this value for the semielliptic form. Furthermore, this expected linear behavior is only accurate for  $kT \ll 0.05E_c$ . These results are in agreement with the computer simulations of Kearney.<sup>5</sup>

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